

NP60N04VUK-E1-AY

NP60N04VUK-E1-AY Information



For Reference Only

Part Number NP60N04VUK-E1-AY

Manufacturer Renesas Electronics America

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 40V 60A TO-252

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NP60N04VUK-E1-AY Specifications

Manufacturer Part Number NP60N04VUK-E1-AY Manufacturer Renesas Electronics America Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 63nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3680pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.2W (Ta), 105W (Tc) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 63nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3680pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.2W (Ta), 105W (Tc) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer	Renesas Electronics America
PackageTO-252-3, DPak (2 Leads + Tab), SC-63Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3680pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta), 105W (Tc)Rds On (Max) @ Id, Vgs3.85 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Category	Discrete Semiconductor Products
Series - N-Channel FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 63nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3680pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 1.2W (Ta), 105W (Tc) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package 7O-252 Package / Case 1TO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3680pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta), 105W (Tc)Rds On (Max) @ Id, Vgs3.85 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
Technology Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 63nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 420V FET Feature - Power Dissipation (Max) 1.2W (Ta), 105W (Tc) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3680pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta), 105W (Tc)Rds On (Max) @ Id, Vgs3.85 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 60A (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3680pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta), 105W (Tc)Rds On (Max) @ Id, Vgs3.85 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case 4V @ 250μA 4V @ 250μA 63nC @ 10V 3680pF @ 25V +20V FET (TJ) Surface Mount To-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	60A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature I175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case 63nC @ 10V 3680pF @ 25V 120V 120	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta), 105W (Tc)Rds On (Max) @ Id, Vgs3.85 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	63nC @ 10V
FET Feature - Power Dissipation (Max) 1.2W (Ta), 105W (Tc) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	3680pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.85 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case 1.2W (Ta), 105W (Tc) 3.85 mOhm @ 30A, 10V Surface Mount Trype Surface Mount TO-252 TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.85 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	1.2W (Ta), 105W (Tc)
Mounting Type Surface Mount TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	3.85 mOhm @ 30A, 10V
Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

NP60N04VUK-E1-AY Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NP60N04VUK-E1-AY Payment Methods



















NP60N04VUK-E1-AY Shipping Methods













If you have any question about NP60N04VUK-E1-AY, please do not hesitate to contact us!

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